

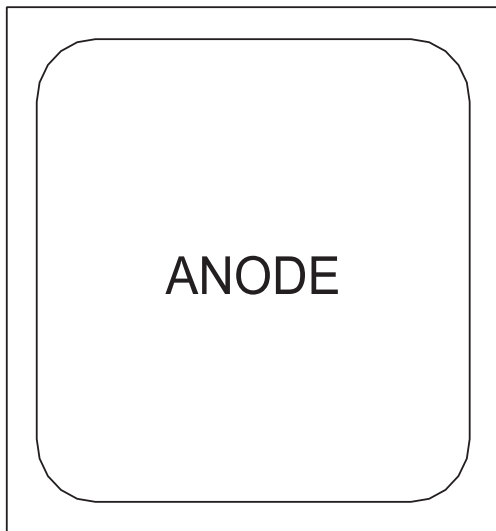
PROCESS CPD17
Ultra Fast Rectifier
3 Amp Glass Passivated Rectifier Chip



PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	88 x 88 MILS
Die Thickness	14 MILS
Anode Bonding Pad Area	69 x 69 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER

1,200

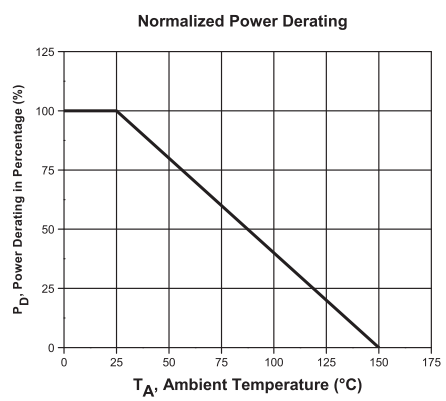
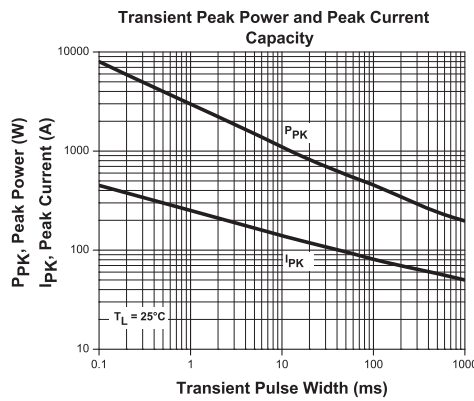
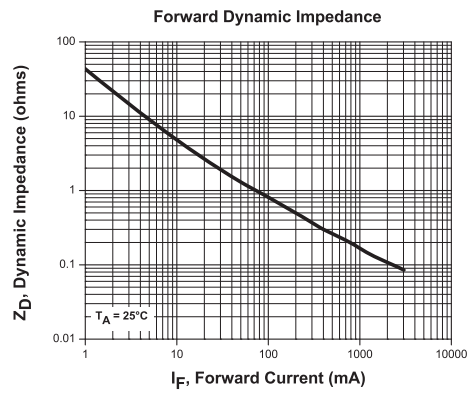
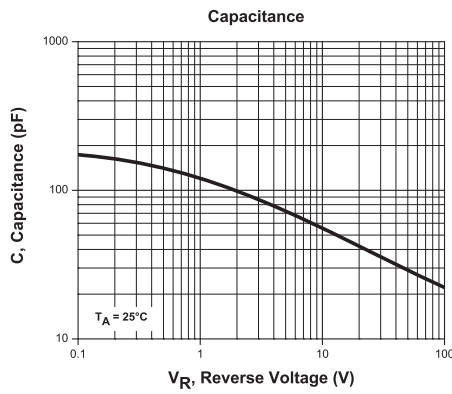
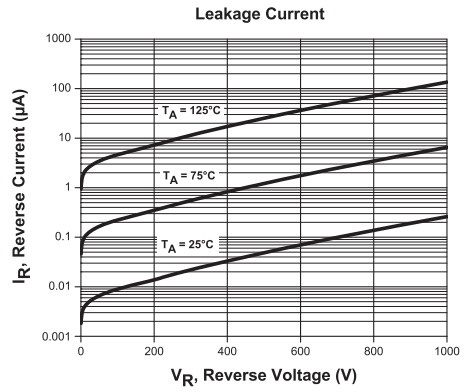
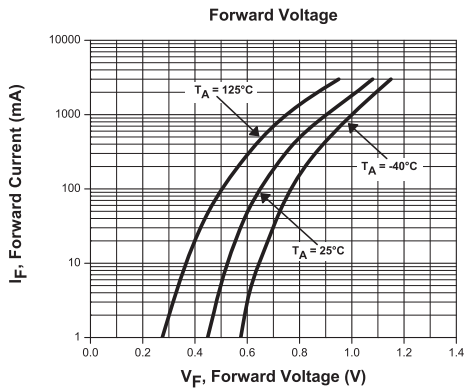
PRINCIPAL DEVICE TYPES

1N5802 thru 1N5806
UES1101 thru UES1106
CMR3U-01 Series

R4 (22-March 2010)

PROCESS CPD17

Typical Electrical Characteristics



R4 (22-March 2010)